

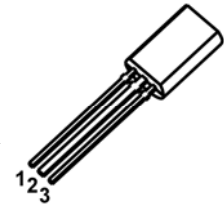
FTC3228 TRANSISTOR (NPN)

FEATURES

- High Voltage
- Large Collector Current Capability
- Complementary to FTA1275

TO – 92L

- 1. EMITTER
- 2. COLLECTOR
- 3. BASE



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	160	V
V _{CEO}	Collector-Emitter Voltage	160	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current	1	A
P _C	Collector Power Dissipation	750	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	167	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 1mA, I _E =0	160			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	160			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =1mA, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =150V, I _E =0			1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =6V, I _C =0			1	μA
DC current gain	h _{FE}	V _{CE} =5V, I _C =200mA	60		320	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =500mA, I _B =50mA			1.5	V
Base-emitter voltage	V _{BE}	V _{CE} =5V, I _C =5mA	0.45		0.75	V
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz			20	pF
Transition frequency	f _T	V _{CE} =5V, I _C =200mA	20			MHz

CLASSIFICATION OF h_{FE}

RANK	R	O	Y
RANGE	60-120	100-200	160-320